### VS-25TTS08FP-M3, VS-25TTS12FP-M3

Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub> 16 A				
$V_{DRM}/V_{RRM}$	800 V, 1200 V			
$V_{TM}$	1.25 V			
I <sub>GT</sub>	45 mA			
$T_J$	-40 °C to 125 °C			
Package	3L TO-220 FullPAK			
Circuit configuration	Single SCR			

#### **FEATURES**

- Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Δ.		
I <sub>RMS</sub>		25	Α		
V <sub>RRM</sub> /V <sub>DRM</sub>		800, 1200	V		
I <sub>TSM</sub>		350	A		
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
T <sub>J</sub>		-40 to +125	°C		

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-25TTS08FP-M3	800	800	10			
VS-25TTS12FP-M3	1200	1200				



# VS-25TTS08FP-M3, VS-25TTS12FP-M3

# Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
PANAMETEN	STIVIDOL	TEST CONDITIONS	TYP. MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 51$ °C, 180° conduction half sine wave	16	
Maximum RMS on-state current	I <sub>RMS</sub>		25	Α
Maximum peak, one-cycle,	ı	10 ms sine pulse, rated V <sub>RRM</sub> applied	300	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	350	
Maximum 12t fau fuaina	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	450	A2a
Maximum I <sup>2</sup> t for fusing	I-l	10 ms sine pulse, no voltage reapplied	630	A <sup>2</sup> s
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1ms to 10 ms, no voltage reapplied	6300	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C	1.25	V
On-state slope resistance	r <sub>t</sub>	T <sub>.I</sub> = 125 °C	12.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	1j=125 C	1.0	V
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$T_J = 25 ^{\circ}\text{C}$ $V_B = \text{Rated } V_{BBM}/V_{DBM}$	0.5	
waxiinuiii reverse and direct leakage current	'RM/ 'DM	T <sub>J</sub> = 125 °C	10	
Holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 $^{\circ}$ C	- 150	mA
Maximum latching current	lι	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		V/µs
Maximum rate of rise of turned-on current	dI/dt		150	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>		8.0	w
Maximum average gate power	P <sub>G(AV)</sub>		2.0	- vv
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	٧
Maximum required DC gate current to trigger	l <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20	
Maximum vaguired DC gata		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	Ī ,,
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V <sub>GD</sub>		0.25	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	4	μs
Typical turn-off time	t <sub>q</sub>	1j = 125 C	110	



### www.vishay.com

## Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		-40 to 125	°C
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		$R_{\text{thCS}}$	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
Wounting torque	maximum			12 (10)	(lbf ⋅ in)
Marking device		Occasional TO 2000 Full DAM	25TTS0	8FP	
		Case style 3L TO-220 FullPAK	25TTS1:	2FP	

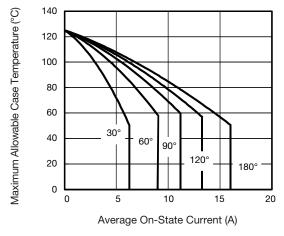


Fig. 1 - Current Rating Characteristics

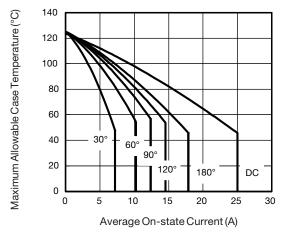


Fig. 2 - Current Rating Characteristics

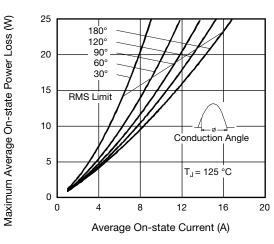


Fig. 3 - On-State Power Loss Characteristics

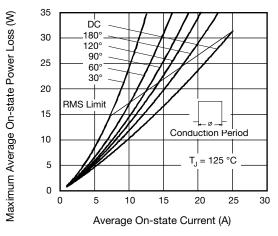


Fig. 4 - On-State Power Loss Characteristics

www.vishay.com

## Vishay Semiconductors

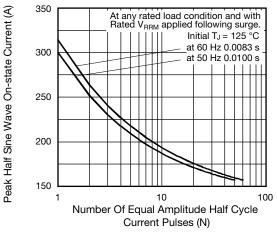


Fig. 5 - Maximum Non-Repetitive Surge Current

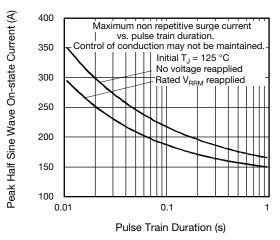


Fig. 6 - Maximum Non-Repetitive Surge Current

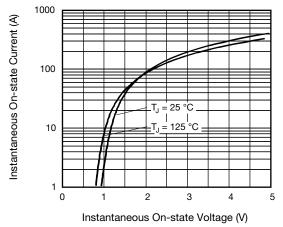


Fig. 7 - On-State Voltage Drop Characteristics

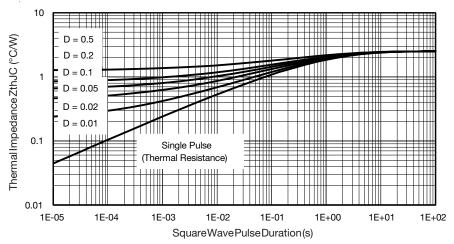


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

## VS-25TTS08FP-M3, VS-25TTS12FP-M3

### Vishay Semiconductors

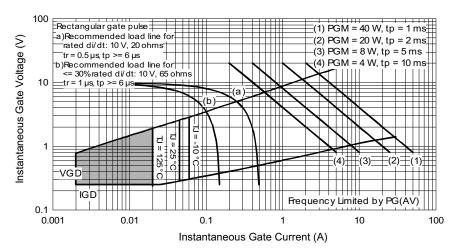
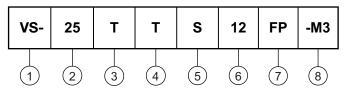


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

### Device code



- 1 Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- 3 Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

Standard recovery rectifier

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes		

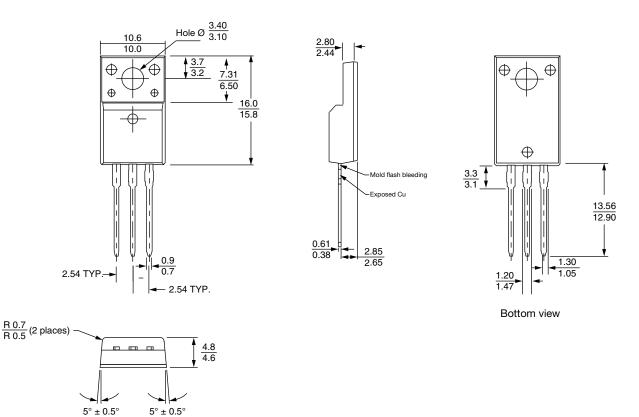
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96155		
Part marking information	www.vishay.com/doc?95456		



Vishay Semiconductors

### **3L TO-220 FullPAK**

### **DIMENSIONS** in millimeters



#### **Notes**

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.